NPN Silicon Epitaxial Planar Transistors

Features

- AEC-Q101 Qualified
- These transistors are subdivided into three groups -16, -25 and -40, according to their current gain.
 As complementary types the PNP transistors BC807 and BC808 are recommended.
- Halogen and Antimony Free(HAF), RoHS compliant

Applications

• For switching, AF driver and amplifier applications



1. Base 2. Emitter 3. Collector SOT-23 Plastic Package

Absolute Maximum	Ratings	(T _a = 25°C)
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Parameter		Symbol	Value	Unit
Collector Base Voltage	BC817 BC818	Vcbo	50 30	V
Collector Emitter Voltage	BC817 BC818	V _{CEO}	45 25	V
Emitter Base Voltage		V _{EBO}	5	V
Collector Current		lc	500	mA
Total Power Dissipation ¹⁾		Ptot	300	mW
Junction Temperature		Tj	150	°C
Storage Temperature Range		T _{stg}	- 55 to + 150	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient ¹⁾	$R_{\theta JA}$	417	°C/W

¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain Current Gain Group -16 at $V_{CE} = 1 V$, $I_C = 100 mA$ Current Gain Group -16 -25 -40 -40	hfe hfe hfe hfe	100 160 250 40	- - -	250 400 600	- - -
Collector Base Cutoff Current at $V_{CB} = 20 \text{ V}$	Ісво	-	-	100	nA
Emitter Base Cutoff Current at V_{EB} = 5 V	I _{EBO}	-	-	100	nA
	V _{(BR)CBO}	50 30	-	-	V
	V _{(BR)CEO}	45 25	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10 \ \mu A$	V _{(BR)EBO}	5	-	-	V
Collector Emitter Saturation Voltage at I_c = 500 mA, I_B = 50 mA	V _{CE(sat)}	-	-	0.7	V
Base Emitter Voltage at I _C = 500 mA, V _{CE} = 1 V	$V_{BE(on)}$	-	-	1.2	V
Transition Frequency at V_{CE} = 5 V, I _C = 10 mA, f = 50 MHz	f⊤	100	-	-	MHz
Collector Base Capacitance at V_{CB} = 10 V, f = 1 MHz	C _{ob}	-	5	-	pF



Electrical Characteristics Curves

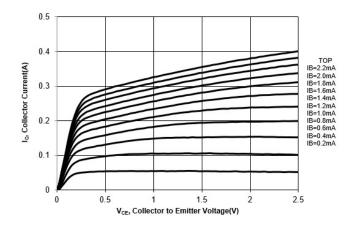


Fig. 1 Output Characteristics Curve

Fig. 2 Collector Current vs. Base to Emitter Voltage

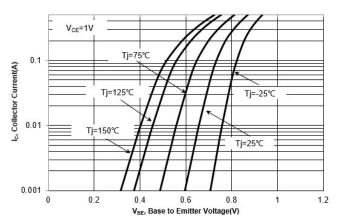
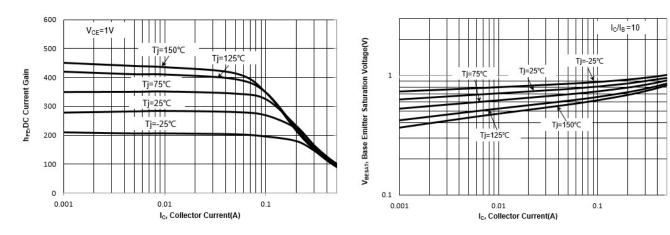


Fig. 3 DC Current Gain vs. Collector Current

Fig. 4 V_{BESAT} vs. Collector Current





Electrical Characteristics Curves

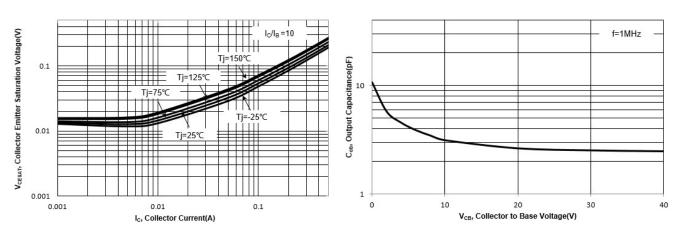
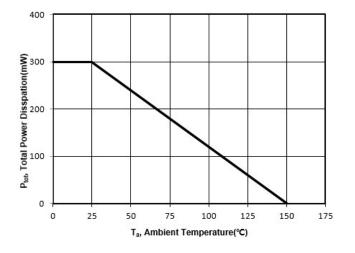


Fig. 5 VCESAT vs. Collector Current

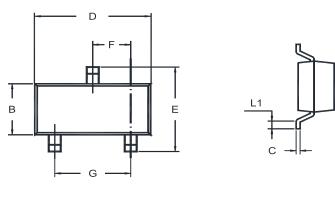
Fig. 6 Output Capacitance

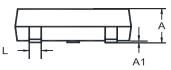
Fig. 7 Power Derating Curve





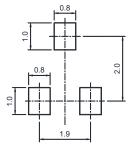
Package Outline (Dimensions in mm)





Unit	А	A1	В	С	D	E	F	G	L	L1
-	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
mm	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

Recommended Soldering Footprint



ΥM

Packing information

Tape Wid		Pit	tch	Reel Size		Des Des I Des leises Oursetites	
Package	(mm)	mm	inch	mm	inch	Per Reel Packing Quantity	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000	

Marking information

Part No.	Marking Code
BC817-16&BC818-16	6CR
BC817-25&BC818-25	6CS
BC817-40&BC818-40	6CT

" • " = HAF (Halogen and Antimony Free)

"YM" = Date Code Marking

"Y" = Year

"M" = Month

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SOT-23